











SN74LVC1G175

SCES560G -MARCH 2004-REVISED JUNE 2015

SN74LVC1G175 Single D-Type Flip-Flop With Asynchronous Clear

Features

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Supports Down Translation to V_{CC}
- Max t_{pd} of 4.3 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- TV/Set Top Box/Audio
- EPOS (Electronic Point-of-Sale)
- **Motor Drives**
- PC/Notebook
- Servers
- **Factory Automation and Control**
- Medical Healthcare and Fitness
- **Smart Grid**
- Telecom Infrastructure
- **Enterprise Switching**
- **Projectors**
- Storage

3 Description

This single D-type flip-flop is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G175 device has an asynchronous clear (CLR) input. When CLR is high, data from the input pin (D) is transferred to the output pin (Q) on the clock's (CLK) rising edge. When CLR is low, Q is forced into the low state, regardless of the clock edge or data on D.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC1G175DBV	SOT-23 (6)	2.90 mm × 1.60 mm		
SN74LVC1G175DCK	SC70 (6)	2.00 mm × 1.25 mm		
SN74LVC1G175DRY	SON (6)	1.45 mm × 1.00 mm		
SN74LVC1G175YZP	DSBGA (6)	1.41 mm × 0.91 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

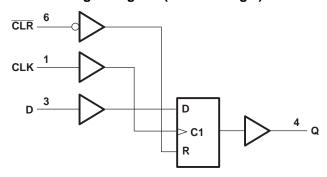




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4 Revision History

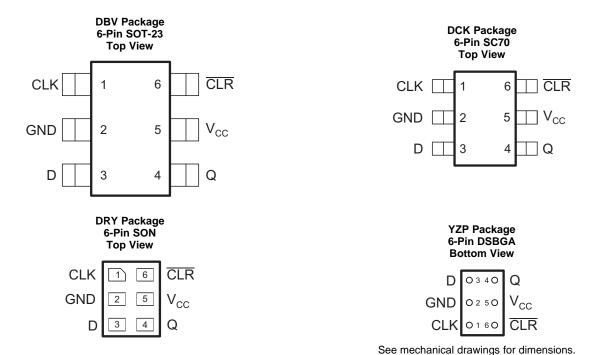
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision F (December 2013) to Revision G				
•	Added Applications	1			
•	Added Device Information table	1			
•	Added ESD Ratingss table	4			
•	Added Thermal Information table	5			
•	Added Typical Characteristics.	7			
_					

CI	Changes from Revision E (June 2008) to Revision F					
•	Updated document to new TI data sheet format	······································				
•	Deleted Ordering Information table.	······································				
•	Updated Features.	·				



5 Pin Configuration and Functions



Pin Functions

PIN		1/0	DESCRIPTION				
NAME	NO.	1/0	DESCRIPTION				
CLK	1	1	Clock Input				
CLR	6	1	Clear Data Input				
D	3	1	Data Input				
GND	2	_	Ground				
Q	4	0	Output				
V _{CC}	5	_	Power				



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT	
V _{CC}	Supply voltage	Supply voltage				
V_{I}	Input voltage		-0.5	6.5	V	
Vo	Voltage applied to any outp	out in the high-impedance or power-off state (2)	-0.5	6.5	V	
Vo	Voltageapplied to any outp	ut in the high or low state (2)(3)	-0.5	V _{CC} + 0.5	V	
I_{IK}	Input clamp current	V _I < 0		-50	mA	
I _{OK}	Output clamp current	V _O < 0		-50	mA	
Io	Continuous output current			±50	mA	
	Continuous current through		±100	mA		
T _{stg}	Storage temperature		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	\/
	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	1000	٧

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V	Supply voltage	Operating		5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		٧
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$		
\/	High lovel input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
V_{IH}	High-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$		
.,		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	
	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
V _{IL}		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		8.0	V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$	
V_{I}	Input voltage		0	5.5	V
V_{O}	Output voltage		0	V_{CC}	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		8	
I_{OH}	High-level output current	V 2.V		-16	mA
		V _{CC} = 3 V		-24	
		V _{CC} = 4.5 V		-32	

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
I _{OL}		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
	Low-level output current	.ow-level output current		16	mA
	$V_{CC} = 3 \text{ V}$ $V_{CC} = 4.5 \text{ V}$		24		
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$		10	
T _A	Operating free-air temperature		-40	125	°C

6.4 Thermal Information

			SN74LV	C1G175		
THERMAL METRIC ⁽¹⁾		DBV (SOT-23)	DCK (SC70)	DRY (SON)	YZP (DSBGA)	UNIT
			6 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	165	259	234	123	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS	v	-40°0	C to 85°C	-40°	-40°C to 125°C		
PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾ M	XX MIN	TYP ⁽¹⁾	MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1		V _{CC} - 0.1			
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		1.2			
N/	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9			V
V _{OH}	$I_{OH} = -16 \text{ mA}$	3 V	2.4		2.4			V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3			
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8			
	I _{OL} = 100 μA	1.65 V to 5.5 V		().1		0.1	
	I _{OL} = 4 mA	1.65 V		0.	45		0.45	
V	I _{OL} = 8 mA	2.3 V		(0.3		0.3	V
V _{OL}	I _{OL} = 16 mA	3 V		().4		0.4	V
	I _{OL} = 24 mA	3 V		0.	55		0.55	
	I _{OL} = 32 mA	4.5 V		0.	55		0.55	
I _I	$V_I = 5.5 \text{ V or GND}$	0 to 5.5 V			±1		±1	μΑ
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±	10		±10	μΑ
I _{cc}	V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10		10	μΑ
ΔI _{CC}	One input at $V_{CC} = 0.6 \text{ V}$, Other inputs at V_{CC} or GND	3 V to 5.5 V		5	00		500	μΑ
C _i	$V_I = V_{CC}$ or GND	3.3 V		3		3		pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



6.6 Timing Requirements, -40°C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

			<u> </u>		, , , , , , , , , , , , , , , , , , , ,							
					-40°C to 85°C							
		V _{CC} = ± 0.1		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{clock}	Clock frequency	Clock frequency			100		125		150		175	MHz
t _w	Pulse duration	CLR	Low	5.6		3		2.8		2.5		
		CLK	High or low	3.5		3		2.8		2.5		ns
	0.1 11 1.1 01.14		·	3		2.5		2		1.5		
t _{su}	Setup time, before CLK↑	CLR in:	active	0		0		0.5		0.5		ns
t _h	Hold time, data after CLK↑			0		0		0.5		0.5		ns

6.7 Timing Requirements, -40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

							−40°C to	125°C				
				V _{CC} = 1 ± 0.1		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5	5 V 5 V	UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{clock}	Clock frequency	frequency					125		150		175	MHz
	Pulse duration	CLR	Low	5.6		3		2.8		2.5		ns
t _w	Pulse duration	CLK	High or low	3.5		3		2.8		2.5		115
	Setup time, before CLK↑	Data		3		2.5		2		1.5		20
t _{su}	usu Setup time, before CLK		CLR inactive			0.5		0.7		0.7		ns
t _h	Hold time, data after CLK↑	0.5		0.5		0.7		0.7		ns		

6.8 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 2)

PARAMETER											
	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			100		125		150		175		MHz
t _{pd}	CLK	0	2.5	12.9	2	6.5	1.4	4.6	1	3	
	CLR	Q	2.5	12.4	2	6	1.2	4.3	1	3.2	ns

6.9 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			100		125		150		175		MHz
t _{pd}	CLK	0	2.7	13.4	2.2	7.1	1.6	5.7	1.5	4	
	CLR	Q	2.7	12.9	2.2	7	1.5	5.8	1.3	4.1	ns



6.10 Switching Characteristics, -40°C to 125°C

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
f _{max}			100		125		150		175		MHz	
	CLK	0	2.7	15.4	2.2	8.1	1.6	6.7	1.5	5		
t _{pd}	CLR	Q	2.7	14.9	2.2	8	1.5	6.8	1.3	5.1	ns	

6.11 Operating Characteristics

 $T_A = 25$ °C

	PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	$V_{CC} = 5 V$	UNIT
	FARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	18	19	19	21	pF

6.12 Typical Characteristics

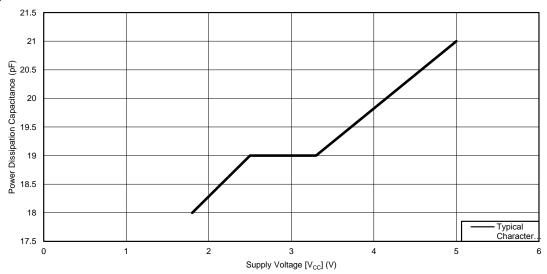
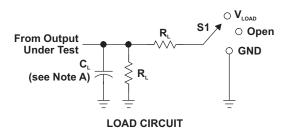


Figure 1. Voltage vs Capacitance

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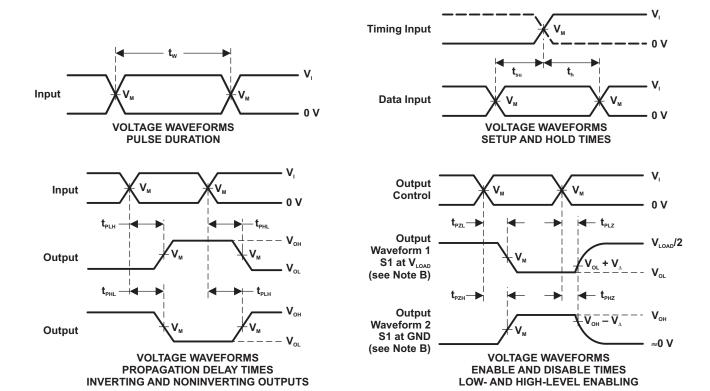


7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

.,	INI	PUTS	.,	.,		_	.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$2.5~V~\pm~0.2~V$	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$3.3~V\pm0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

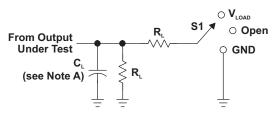
Figure 2. Load Circuit and Voltage Waveforms

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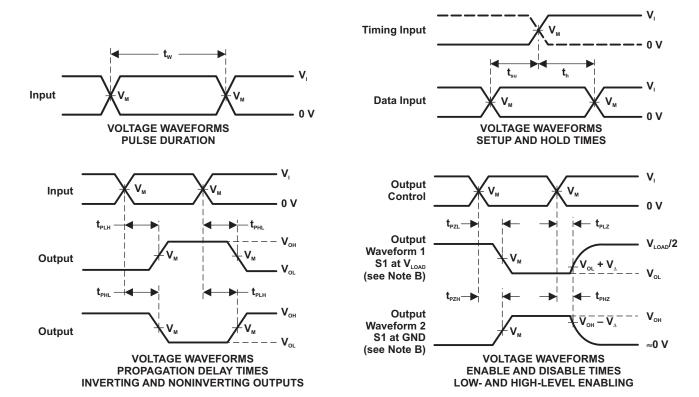
Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

,,	INI	PUTS		V			.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \,\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. $t_{\text{PLH}}^{\text{F2L}}$ and $t_{\text{PHL}}^{\text{F2L}}$ are the same as $t_{\text{pd}}^{\text{eff}}$
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

Product Folder Links: SN74LVC1G175



8 Detailed Description

8.1 Overview

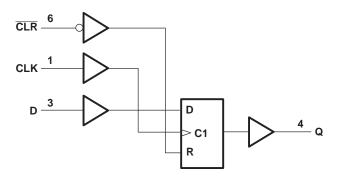
This single D-type flip-flop is designed for 1.65-V to 5.5-V $V_{\rm CC}$ operation.

The SN74LVC1G175 device has an asynchronous clear ($\overline{\text{CLR}}$) input. When $\overline{\text{CLR}}$ is high, data from the input pin (D) is transferred to the output pin (Q) on the clock's (CLK) rising edge. When $\overline{\text{CLR}}$ is low, Q is forced into the low state, regardless of the clock edge or data on D.

NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74LVC1G175 device has a wide operating V_{CC} range of 1.65 V to 5.5 V, which allows it to be used in a broad range of systems. The 5.5-V I/Os allow down translation and also allow voltages at the inputs when $V_{CC} = 0$.

8.4 Device Functional Modes

Table 1 lists the functional modes for SN74LVC1G175.

Table 1. Function Table

	INPUTS	OUTPUT	
CLR	CLK	D	Q
Н	1	L	Г
Н	1	Н	Н
Н	H or L	X	Q_0
L	X	X	L

Product Folder Links: SN74LVC1G175



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Multiple SN74LVC1G175 devices can be used in tandem to create a shift register of arbitrary length. In this example, we use four SN74LVC1G175 devices to form a 4-bit serial shift register. By connecting all CLK inputs to a common clock pulse and tying each output of one device to the next, we can store and load 4-bit values on demand. We demonstrate loading the 4 bit value 1101 into memory by setting Serial Input Data to each desired memory bit, and by sending a clock pulse for each bit, we sequentially move all stored bits from left to right $(A \rightarrow B \rightarrow C \rightarrow D)$

9.2 Typical Application

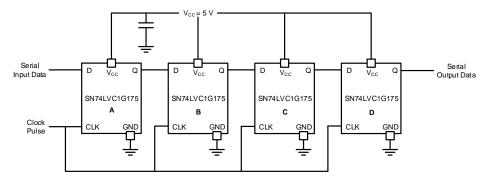


Figure 4. 4-Bit Serial Shift Register

Serial Input Data	Stored A	Stored B	Stored C	Stored D
1	0	0	0	0
0	1	0	0	0
1	0	1	0	0
1	1	0	1	0
0	1	1	0	1

Table 2. Stored Data Values

9.2.1 Design Requirements

The SN74LVC1G175 device uses CMOS technology and has balanced output drive. Care must be taken to avoid bus contention because it can drive currents that would exceed maximum limits.

The SN74LVC1G175 allows storing digital signals with a digital control signal. All input signals should remain as close as possible to either 0 V or V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

- 1. Recommended input conditions:
 - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the table.
 - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended output conditions:
 - Load currents should not exceed ±50 mA.



3. Frequency selection criterion:

- The effects of frequency upon the output current should be studied in Figure 5.
- Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the *Layout* section.

9.2.3 Application Curve

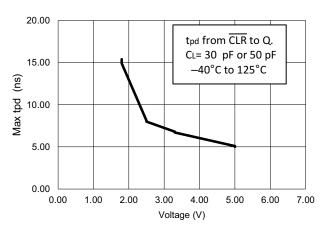


Figure 5. Max tpd vs Voltage of LVC Family

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple-bit logic devices, inputs must never float.

In many cases, functions (or parts of functions) of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or when only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected, because the undefined voltages at the outside connections result in undefined operational states. Figure 6 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally they are tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it disables the output section of the part when asserted, which does not disable the input section of the I/Os. Therefore, the I/Os cannot float when disabled.



11.2 Layout Example

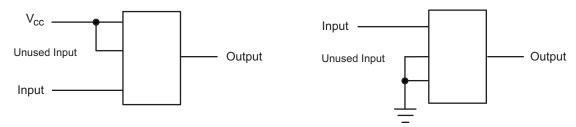


Figure 6. Layout Diagram

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(-)		Ū			(=)	(6)	(-)		()	
74LVC1G175DBVRE4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	(C755, C75R)	Samples
74LVC1G175DBVRG4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	(C755, C75R)	Samples
74LVC1G175DCKRG4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D65	Samples
74LVC1G175DCKTG4	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D65	Samples
SN74LVC1G175DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C755, C75R)	Samples
SN74LVC1G175DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C755, C75R)	Samples
SN74LVC1G175DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(D65, D6J, D6R)	Samples
SN74LVC1G175DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(D65, D6J, D6R)	Samples
SN74LVC1G175DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D6	Samples
SN74LVC1G175YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	D6N	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: Til defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC1G175:

Enhanced Product: SN74LVC1G175-EP

NOTE: Qualified Version Definitions:

• Enhanced Product - Supports Defense, Aerospace and Medical Applications



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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G175DCKRG4	SC70	DCK	6	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
74LVC1G175DCKTG4	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G175DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G175DBVT	SOT-23	DBV	6	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G175DBVT	SOT-23	DBV	6	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G175DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G175DCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74LVC1G175DCKT	SC70	DCK	6	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G175DCKT	SC70	DCK	6	250	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
SN74LVC1G175DCKT	SC70	DCK	6	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G175DRYR	SON	DRY	6	5000	180.0	8.4	1.2	1.65	0.69	4.0	8.0	Q1
SN74LVC1G175YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G175DCKRG4	SC70	DCK	6	3000	180.0	180.0	18.0
74LVC1G175DCKTG4	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G175DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
SN74LVC1G175DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
SN74LVC1G175DBVT	SOT-23	DBV	6	250	202.0	201.0	28.0
SN74LVC1G175DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1G175DCKR	SC70	DCK	6	3000	202.0	201.0	28.0
SN74LVC1G175DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G175DCKT	SC70	DCK	6	250	202.0	201.0	28.0
SN74LVC1G175DCKT	SC70	DCK	6	250	180.0	180.0	18.0
SN74LVC1G175DRYR	SON	DRY	6	5000	200.0	183.0	25.0
SN74LVC1G175YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



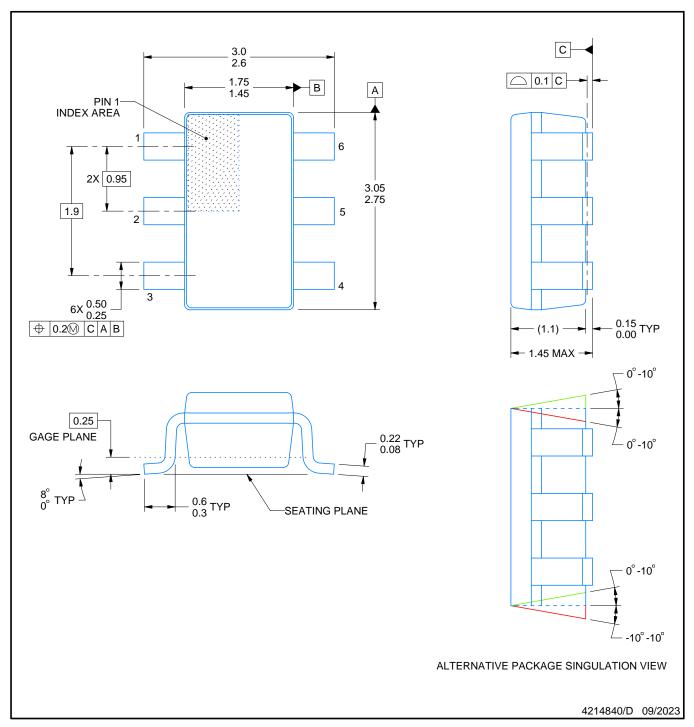
NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

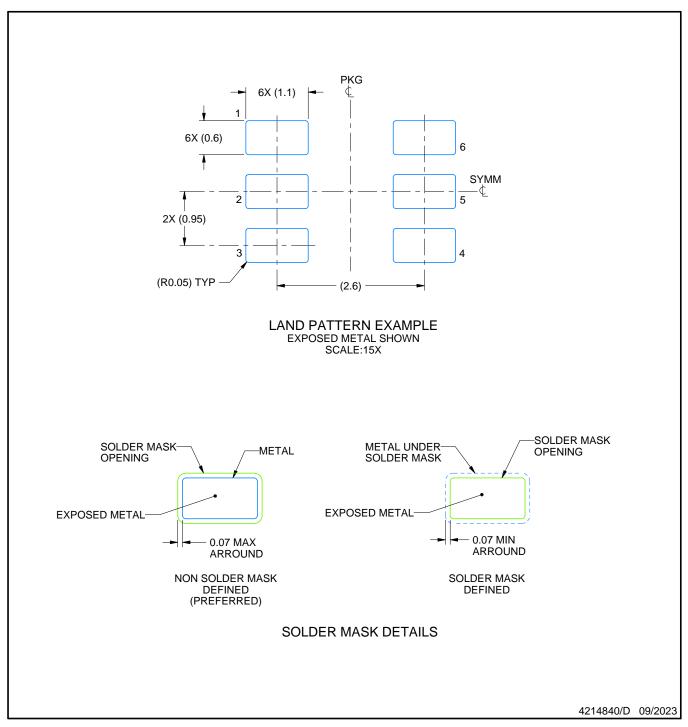
 2. This drawing is subject to change without notice.

 3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- 5. Refernce JEDEC MO-178.



SMALL OUTLINE TRANSISTOR



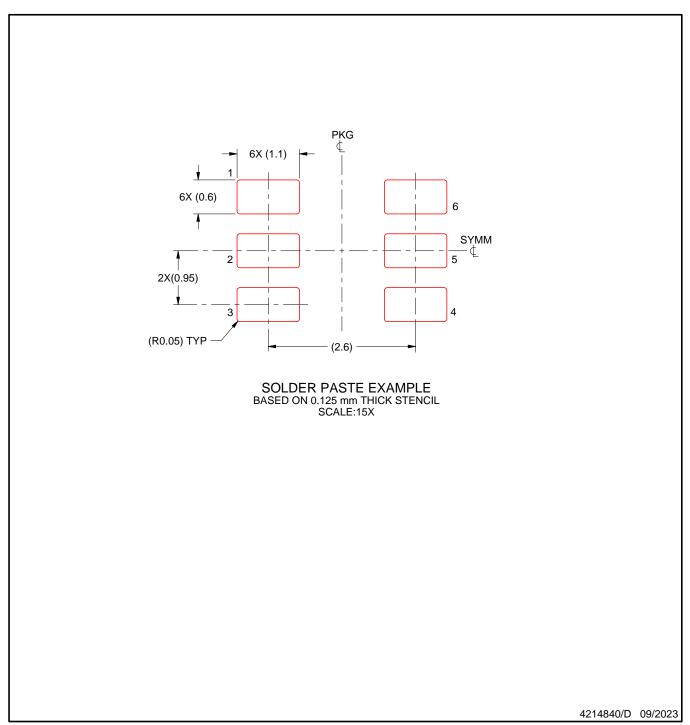
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



DCK (R-PDSO-G6)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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